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64. (Amended) A wordline construction, comprising:
a conductive gate having sidewalls; and
sidewall spacers extending along the sidewalls of the conductive gate, the
sidewall spacers being essentially free of nitrogen and having thicknesses of less
than or equal to about 500Å.

65. The wordline of claim 64 wherein the sidewall spacers comprise from
about 2% to about 20% carbon (by weight).

66. The wordline of claim 65 wherein the sidewall spacers further
comprise silicon and oxygen.

67. (Cancelled)

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68. (Amended) A capacitor construction, comprising:
a first electrode extending within an insulative layer, the first electrode
comprising conductively doped silicon; at least a portion of the first electrode
extending along and against a material that comprises from about 2% to about
20% carbon (by weight);
a second electrode proximate the first electrode; and
a dielectric layer between the second electrode and the first electrode.

70. The capacitor construction of claim 68 wherein the material comprises silicon and carbon.

71. The capacitor construction of claim 68 wherein the material comprises silicon carbide.

72. The capacitor construction of claim 68 wherein the material comprises silicon, oxygen and the carbon.

NE
73. The capacitor construction of claim 68 wherein the material consists essentially of silicon, oxygen and the carbon.

74. The capacitor construction of claim 68 wherein the material comprises silicon, nitrogen and the carbon.

75. The capacitor construction of claim 68 wherein the material consists essentially of silicon, nitrogen and the carbon.

76. (Amended) A DRAM construction, comprising:

- a pair of wordlines over a substrate, the wordlines comprising sidewall edges;
- sidewall spacers extending along the sidewall edges of the wordlines;
- three nodes proximate the wordlines, the three nodes comprising a first node, second node and third node, the second node being in gated electrical connection with the first node through one of the wordlines and being in gated electrical connection with the third node through the other of the wordlines;
- a carbon-containing material proximate the wordlines, the carbon-containing material comprising from about 2% to about 20% carbon, and being essentially free of nitrogen;
- an insulative layer over the carbon-containing material;
- a first capacitor construction in electrical connection with the first node, the first capacitor construction comprising a first storage node;
- a second capacitor construction in electrical connection with the third node, the second capacitor construction comprising a second storage node; and
- a bit line contact in electrical connection with the second node, at least one of the first storage node, second storage node and bit line contact being in physical contact with the carbon-containing material.

77. The DRAM construction of claim 76 wherein the carbon-containing material is over the wordlines.

78. (Cancelled)

79. The DRAM construction of claim 76 wherein at least the sidewall spacers comprise the carbon-containing material.

80. The DRAM^{NE} construction of claim 76 wherein the carbon-containing material is adjacent the wordlines as sidewall spacers along sidewall edges of the wordlines and comprises silicon, oxygen and carbon.

81. The DRAM construction of claim 76 wherein the carbon-containing material comprises silicon carbide.

83. The DRAM construction of claim 76 wherein the carbon-containing material comprises silicon, oxygen and carbon.

84. The DRAM construction of claim 76 wherein the carbon-containing material consists essentially of silicon, oxygen and carbon.

85. (Cancelled)

86. (Cancelled)

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87. (New) A semiconductor construction comprising:

- a semiconductor substrate;
- a pair of conductive gates over the substrate, the conductive gates having sidewalls;
- a node location between the pair of conductive gates;
- a carbon-containing material extending along the sidewalls of the wordlines;

and

- an insulative material over the wordlines and over at least some of the carbon-containing material, at least a portion of the insulative material being directly against the wordlines.

88. (New) The semiconductor construction of claim 87 further comprising:

- an opening in the insulative material between the pair of wordlines, the opening having a base comprising a surface of the substrate; and
- a capacitor construction within the opening and directly against the surface of the substrate.

89. (New) The semiconductor construction of claim 87 wherein the carbon containing material comprises from about 2% to about 20% carbon (by weight).

90. (New) The semiconductor construction of claim 89 wherein the carbon-containing material further comprises silicon and oxygen.

91. (New) The semiconductor construction of claim 89 wherein the carbon-containing material consists essentially of silicon, oxygen and carbon.

92. (New) The semiconductor construction of claim 89 wherein the carbon-containing material further comprises silicon and nitrogen.

93. (New) The semiconductor construction of claim 89 wherein the carbon-containing material consists essentially of silicon, nitrogen and carbon.

94. (New) The semiconductor construction of claim 87 wherein the carbon-containing material is shaped into sidewall spacers having a thicknesses of less than or equal to about 500 Å.